

TOSHIBA Field-Effect Transistor Silicon N-Channel MOS Type

SSM3K128TU

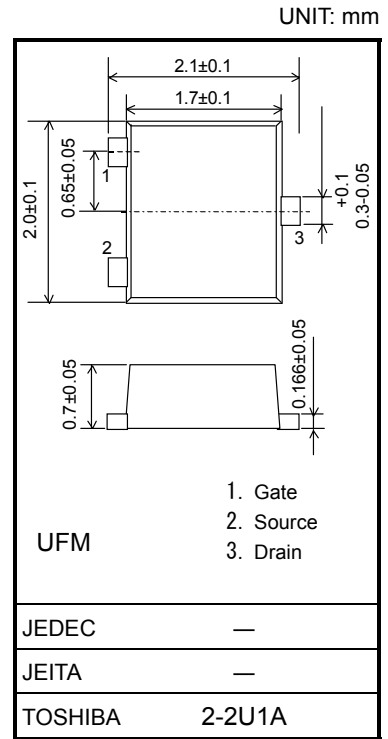
- High-Speed Switching Applications
- Power Management Switch Applications

- 4.0V drive
- Low ON-resistance : $R_{on} = 360\text{m}\Omega$ (max) (@ $V_{GS} = 4.0\text{V}$)
: $R_{on} = 217\text{m}\Omega$ (max) (@ $V_{GS} = 10\text{V}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	± 20	V
Drain current	DC	I_D	1.5	A
	Pulse	I_{DP}	3.0	
Drain power dissipation		P_D (Note1)	500	mW
Channel temperature		T_{ch}	150	$^\circ\text{C}$
Storage temperature		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$

Note 1: Mounted on an FR4 board
(25.4 mm × 25.4 mm × 1.6 t, Cu Pad: 645 mm²)



Weight: 6.6mg (typ.)

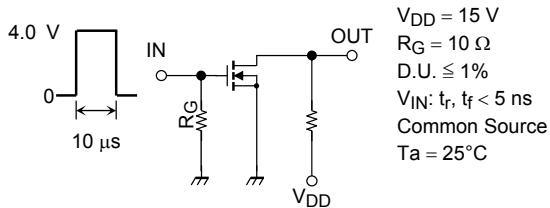
Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	30	—	—	V
Drain cutoff current		I_{DSS}	$V_{DS} = 30\text{ V}$, $V_{GS} = 0\text{ V}$	—	—	1	μA
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16\text{ V}$, $V_{DS} = 0\text{ V}$	—	—	± 1	μA
Gate threshold voltage		V_{th}	$V_{DS} = 5\text{ V}$, $I_D = 1\text{ mA}$	1.1	—	2.6	V
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 5\text{ V}$, $I_D = 0.6\text{ A}$ (Note2)	0.73	1.45	—	S
Drain-source ON-resistance		$R_{DS(ON)}$	$I_D = 0.6\text{ A}$, $V_{GS} = 10\text{ V}$ (Note2)	—	160	217	$\text{m}\Omega$
			$I_D = 0.6\text{ A}$, $V_{GS} = 4.0\text{ V}$ (Note2)	—	260	360	
Input capacitance		C_{iss}	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	—	57	—	pF
Output capacitance		C_{oss}		—	33	—	
Reverse transfer capacitance		C_{rss}		—	12	—	
Total Gate Charge		Q_g	$V_{DS} = 15\text{ V}$, $I_D = 1.5\text{ A}$ $V_{GS} = 10\text{ V}$	—	2.8	—	nC
Gate-Source Charge		Q_{gs}		—	1.6	—	
Gate-Drain Charge		Q_{gd}		—	1.2	—	
Switching time	Turn-on time	t_{on}	$V_{DD} = 15\text{ V}$, $I_D = 0.6\text{ A}$, $V_{GS} = 0 \sim 4.0\text{ V}$, $R_G = 10\ \Omega$	—	12.0	—	ns
	Turn-off time	t_{off}		—	6.9	—	
Drain-source forward voltage		V_{DSF}	$I_D = -1.5\text{ A}$, $V_{GS} = 0\text{ V}$ (Note2)	—	-0.85	-1.2	V

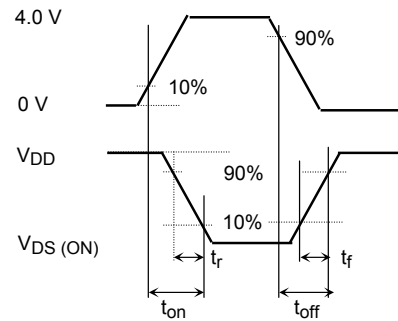
Note 2: Pulse test

Switching Time Test Circuit

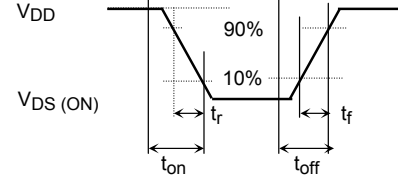
(a) Test Circuit



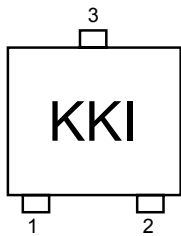
(b) V_{IN}



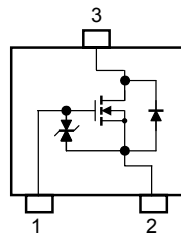
(c) V_{OUT}



Marking



Equivalent Circuit (top view)



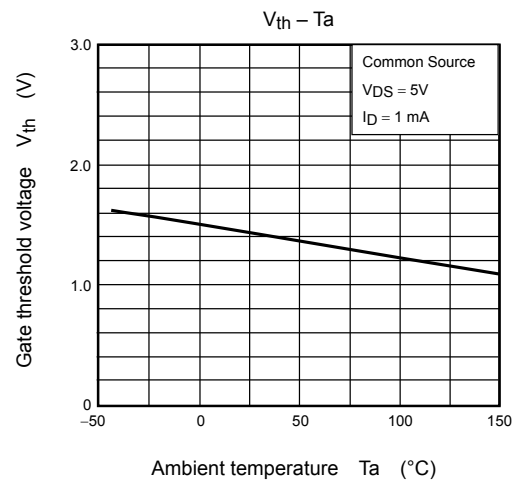
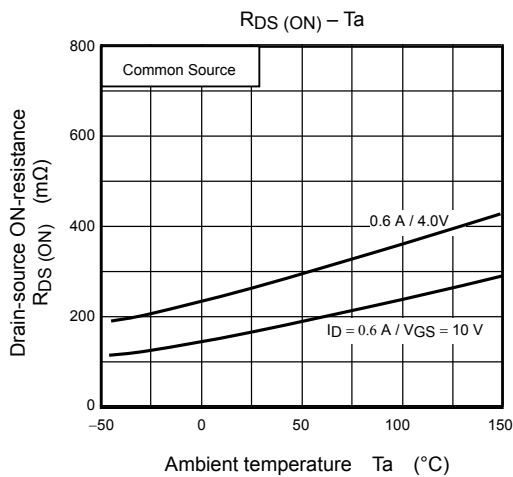
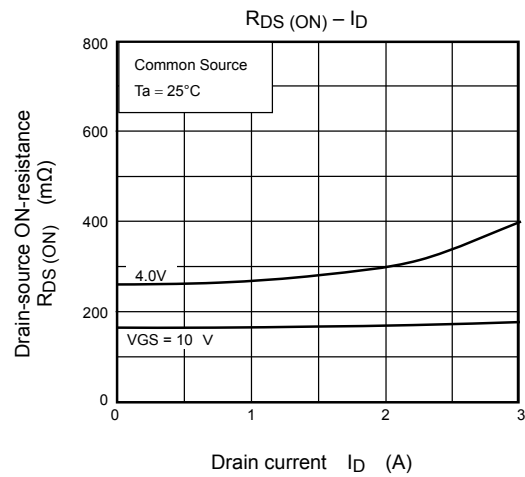
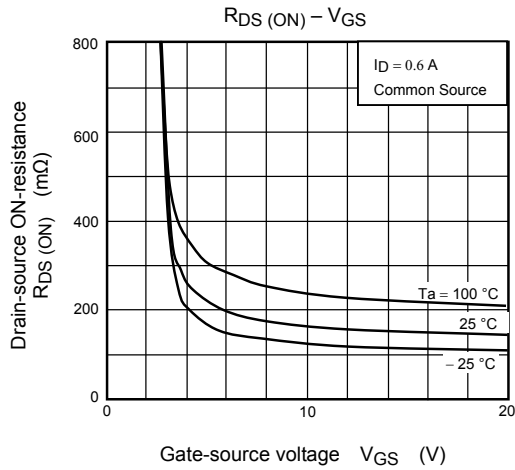
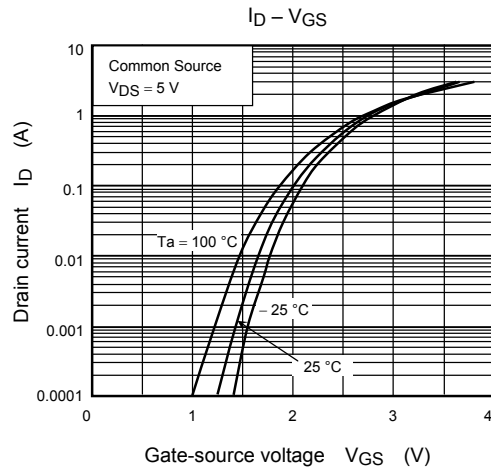
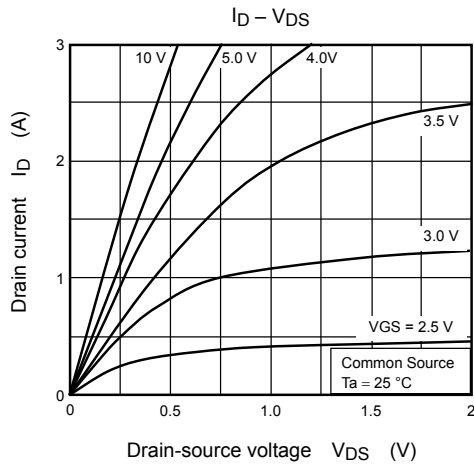
Notice on Usage

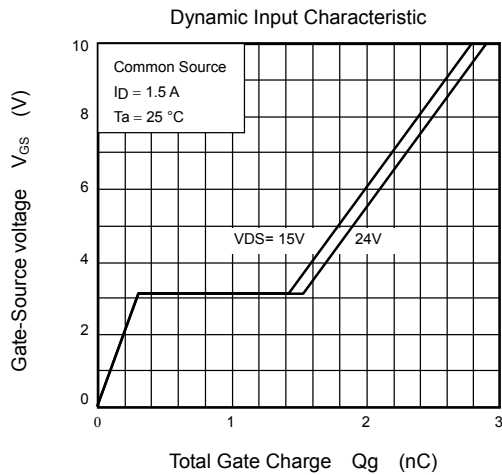
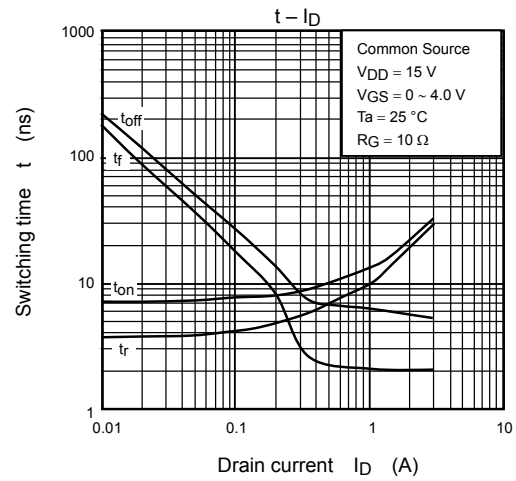
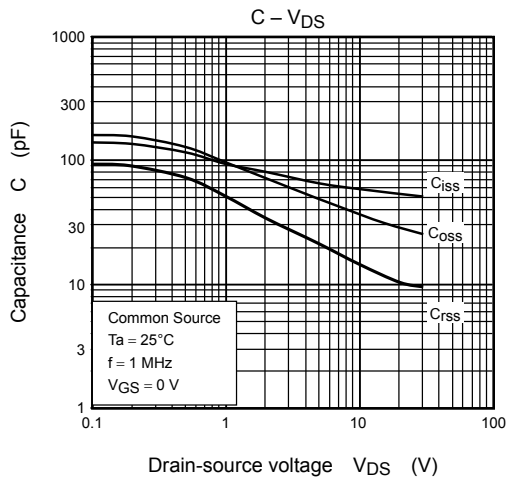
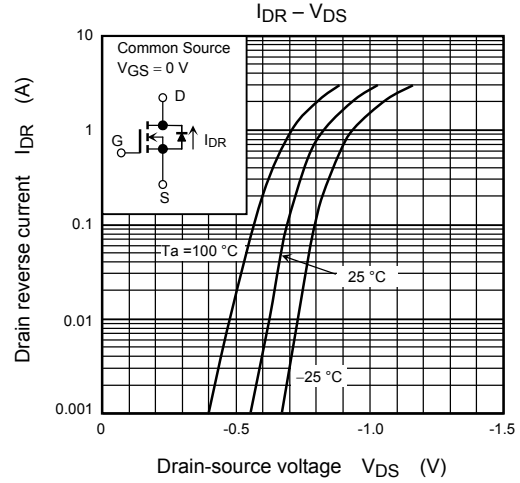
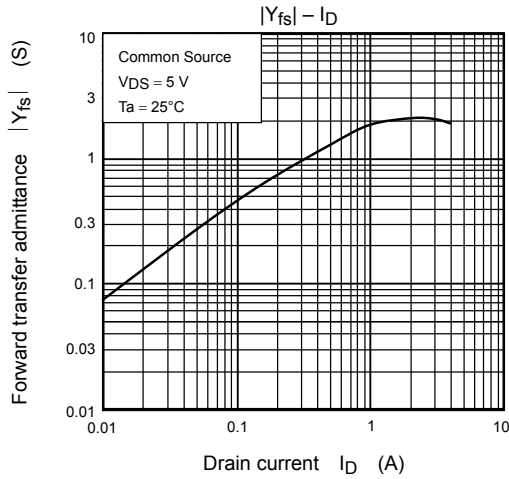
V_{th} can be expressed as the voltage between gate and source when the low operating current value is $I_D = 1\text{ mA}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires a higher voltage than V_{th} and $V_{GS(OFF)}$ requires a lower voltage than V_{th} . (The relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$.)

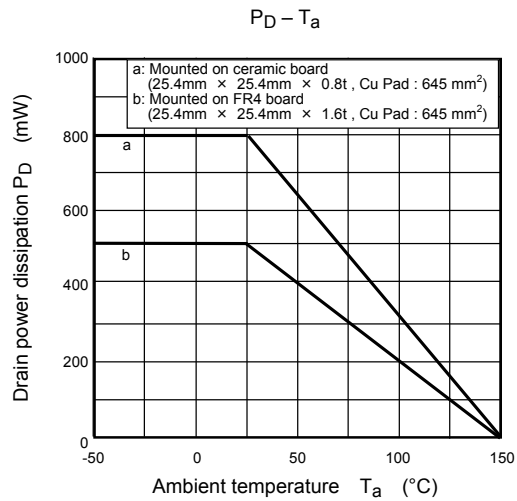
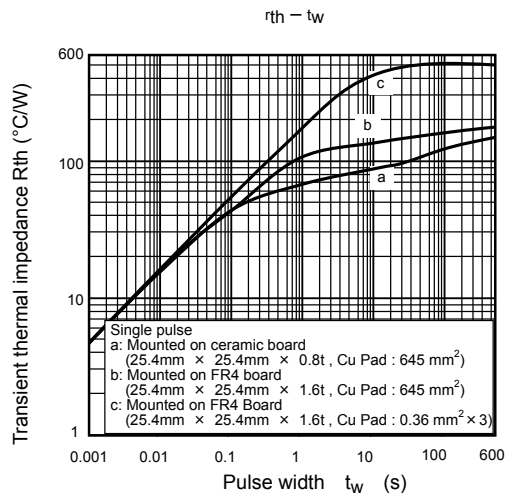
Take this into consideration when using the device.

Handling Precaution

When handling individual devices that are not yet mounted on a circuit board, make sure that the environment is protected against electrostatic discharge. Operators should wear antistatic clothing, and containers and other objects that come into direct contact with devices should be made of antistatic materials.







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20070701-EN

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